
4. (Amended) A method of manufacturing a semiconductor device comprising the steps of:

forming a semiconductor film comprising amorphous silicon on an insulating surface;

B 2 forming a crystallization promoting material comprising a metal in contact with said semiconductor film; and

crystallizing said semiconductor film by heating said semiconductor film;

wherein the step of forming the crystallization promoting material and the step of crystallizing said semiconductor film are conducted successively in a same chamber without exposing said semiconductor film and said crystallization promoting material to the air outside said chamber.

7. (Amended) A method of manufacturing a semiconductor device comprising

B 3 the steps of:

forming a semiconductor film comprising amorphous silicon on an insulating surface;

forming a crystallization promoting material comprising a metal in contact with said semiconductor film by using a vapor of a gas containing said metal in a chamber; and

crystallizing said semiconductor film in contact with said crystallization promoting material in said chamber,

wherein the step of crystallizing said semiconductor film is carried out successively after the formation of said crystallization promoting material without exposing said semiconductor film and said crystallization promoting material to the air outside said chamber.

B 4 10. (Amended) A method of manufacturing a semiconductor device comprising the steps of:

forming a semiconductor film comprising amorphous silicon on an insulating surface;

forming a crystallization promoting material comprising a metal in contact with a selected portion of said semiconductor film in a chamber; and

crystallizing said semiconductor film in contact with said crystallization promoting material in said chamber,

B5
wherein the step of crystallizing said semiconductor film is carried out successively after the formation of said crystallization promoting material without exposing said semiconductor film and said crystallization promoting material to the air outside said chamber.

13. (Amended) A method of manufacturing a semiconductor device comprising the steps of:

B5
forming a semiconductor film comprising amorphous silicon on an insulating surface;
forming a crystallization promoting material comprising a metal in contact with a selected portion of said semiconductor film; and

crystallizing said semiconductor film by heating said semiconductor film;
wherein the step of forming the crystallization promoting material and the step of crystallizing said semiconductor film are conducted successively in a same chamber without exposing said semiconductor film and said crystallization promoting material to the air outside said chamber.

16. (Amended) A method of manufacturing a semiconductor device comprising the steps of:

B6
forming a semiconductor film comprising amorphous silicon on an insulating surface;
forming a crystallization promoting material comprising a metal in contact with a selected portion of said semiconductor film by using a vapor of a gas containing said metal in a chamber; and

crystallizing said semiconductor film in contact with said crystallization promoting material in said chamber,

wherein the step of crystallizing said semiconductor film is carried out successively after the formation of said crystallization promoting material without exposing said semiconductor film and said crystallization promoting material to the air outside said chamber.